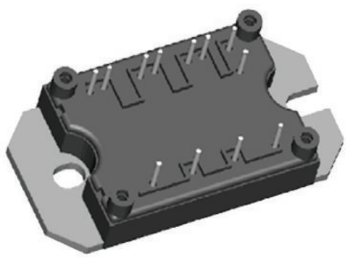
"Half Bridge" IGBT MTP (Ultrafast NPT IGBT), 80 A



MTP

FEATURES

Pb-free Available
RoHS* Available

- Ultrafast Non Punch Through (NPT) technology
- Positive $V_{CE(on)}$ temperature coefficient
- 10 μs short circuit capability
- Square RBSOA
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery and low V_F
- Al_2O_3 DBC
- Optional SMD thermistor (NTC)
- Very low stray inductance design for high speed operation
- UL approved file E78996
- Speed 8 kHz to 60 kHz
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Note
* This datasheet provides information about parts that are RoHS-compliant and/or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information/tables in this datasheet for details.

PRODUCT SUMMARY	
V_{CES}	1200 V
$V_{CE(on)}$ typical at V_{GE} = 15 V	3.36 V
I_C at T_C = 25 °C	80 A
Package	MTP
Circuit	Half bridge

BENEFITS

- Optimized for welding, UPS and SMPS applications
- Rugged with ultrafast performance
- Benchmark efficiency above 20 kHz
- Outstanding ZVS and hard switching operation
- Low EMI, requires less snubbing
- Excellent current sharing in parallel operation
- Direct mounting to heatsink
- PCB solderable terminals
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter breakdown voltage	V_{CES}		1200	V
Continuous collector current	I_C	T_C = 25 °C	80	A
		T_C = 104 °C	40	
Pulsed collector current	I_{CM}		160	
Clamped inductive load current	I_{LM}		160	
Diode continuous forward current	I_F	T_C = 105 °C	21	
Diode maximum forward current	I_{FM}		160	
Gate to emitter voltage	V_{GE}		± 20	V
RMS isolation voltage	V_{ISOL}	Any terminal to case, t = 1 min	2500	
Maximum power dissipation (only IGBT)	P_D	T_C = 25 °C	463	W
		T_C = 100 °C	185	

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Collector to emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0 V, I_C = 250 μA	1200	-	-	V
Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$	V_{GE} = 0 V, I_C = 3 mA (25 °C to 125 °C)	-	+ 1.1	-	V/°C
Collector to emitter saturation voltage	$V_{CE(on)}$	V_{GE} = 15 V, I_C = 40 A	-	3.36	3.59	V
		V_{GE} = 15 V, I_C = 80 A	-	4.53	4.91	
		V_{GE} = 15 V, I_C = 40 A, T_J = 150 °C	-	3.88	4.10	
		V_{GE} = 15 V, I_C = 80 A, T_J = 150 °C	-	5.35	5.68	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, I_C = 500 μA	4	-	6	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, I_C = 1 mA (25 °C to 125 °C)	-	- 12	-	mV/°C
Transconductance	g_{fe}	V_{CE} = 50 V, I_C = 40 A, PW = 80 μs	-	35	-	S
Zero gate voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 25 °C	-	-	250	μA
		V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 125 °C	-	0.4	1.0	mA
		V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 150 °C	-	0.2	10	
Gate to emitter leakage current	I_{GES}	V_{GE} = ± 20 V	-	-	± 250	nA

SWITCHING CHARACTERISTICS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Total gate charge (turn-on)	Q_g	I_C = 40 A V_{CC} = 600 V V_{GE} = 15 V	-	399	599	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	43	65	
Gate to collector charge (turn-on)	Q_{gc}		-	187	281	
Turn-on switching loss	E_{on}	V_{CC} = 600 V, I_C = 40 A, V_{GE} = 15 V, R_g = 5 Ω, L = 200 μH, T_J = 25 °C, energy losses include tail and diode reverse recovery	-	1.14	1.71	mJ
Turn-off switching loss	E_{off}		-	1.35	2.02	
Total switching loss	E_{tot}		-	2.49	3.73	
Turn-on switching loss	E_{on}	V_{CC} = 600 V, I_C = 40 A, V_{GE} = 15 V, R_g = 5 Ω, L = 200 μH, T_J = 125 °C, energy losses include tail and diode reverse recovery	-	1.60	2.40	
Turn-off switching loss	E_{off}		-	1.62	2.43	
Total switching loss	E_{tot}		-	3.22	4.82	
Input capacitance	C_{ies}	V_{GE} = 0 V V_{CC} = 30 V f = 1.0 MHz	-	5521	8282	pF
Output capacitance	C_{oes}		-	380	570	
Reverse transfer capacitance	C_{res}		-	171	257	
Reverse bias safe operating area	RBSOA	T_J = 150 °C, I_C = 160 A V_{CC} = 1000 V, V_p = 1200 V R_g = 5 Ω, V_{GE} = + 15 V to 0 V	Fullsquare			
Short circuit safe operating area	SCSOA	T_J = 150 °C, V_{CC} = 900 V, V_p = 1200 V R_g = 5 Ω, V_{GE} = + 15 V to 0 V	10	-	-	μs

DIODE SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Diode forward voltage drop	V_{FM}	I_C = 40 A	-	2.98	3.38	V
		I_C = 80 A	-	3.90	4.41	
		I_C = 40 A, T_J = 125 °C	-	3.08	3.39	
		I_C = 80 A, T_J = 125 °C	-	4.29	4.72	
		I_C = 40 A, T_J = 150 °C	-	3.12	3.42	
Reverse recovery energy of the diode	E_{rec}	V_{GE} = 15 V, R_g = 5 Ω, L = 200 µH V_{CC} = 600 V, I_C = 40 A T_J = 125 °C	-	574	861	µJ
Diode reverse recovery time	t_{rr}		-	120	180	ns
Peak reverse recovery current	I_{rr}		-	43	65	A

THERMISTOR SPECIFICATIONS (40MT120UHTAPbF only)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Resistance	R_0 [(1)]	T_0 = 25 °C	-	30	-	kΩ
Sensitivity index of the thermistor material	β [(1)(2)]	T_0 = 25 °C T_1 = 85 °C	-	4000	-	K

Notes

[(1)] T_0, T_1 are thermistor´s temperatures

[(2)] $\frac{R_0}{R_1} = \exp\left[\beta\left(\frac{1}{T_0} - \frac{1}{T_1}\right)\right]$, temperature in Kelvin

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Operating junction temperature range		T_J		- 40	-	150	°C
Storage temperature range		T_{Stg}		- 40	-	125	
Junction to case	IGBT	R_{thJC}		-	-	0.29	°C/W
	Diode			-	-	0.61	
Case to sink per module		R_{thCS}	Heatsink compound thermal conductivity = 1 W/mK	-	0.06	-	
Clearance [(1)]			External shortest distance in air between 2 terminals	5.5	-	-	mm
Creepage [(2)]			Shortest distance along external surface of the insulating material between 2 terminals	8	-	-	
Mounting torque to heatsink			A mounting compound is recommended and the torque should be checked after 3 hours to allow for the spread of the compound. Lubricated threads.	3 ± 10 %			Nm
Weight				66			g

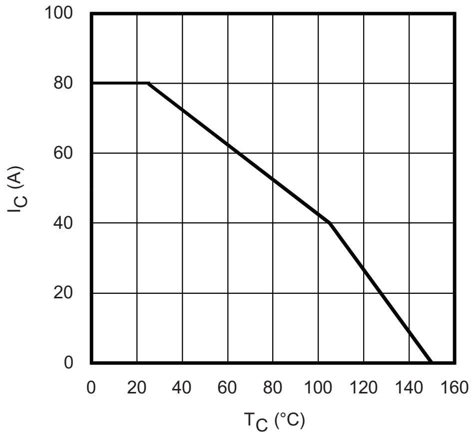


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

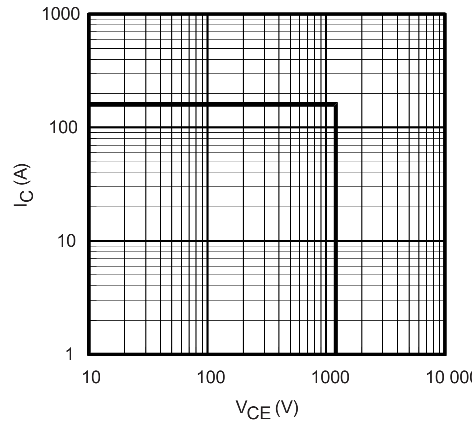


Fig. 4 - Reverse BIAS SOA
T_J = 150 °C; V_{GE} = 15 V

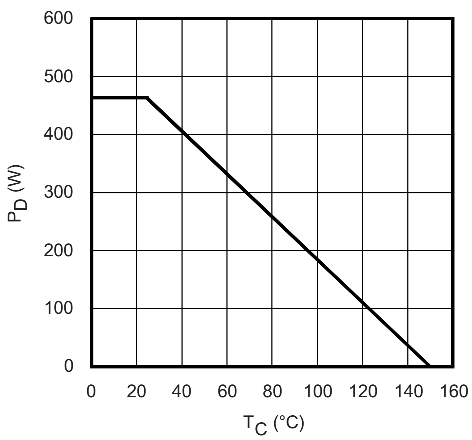


Fig. 2 - Power Dissipation vs. Case Temperature

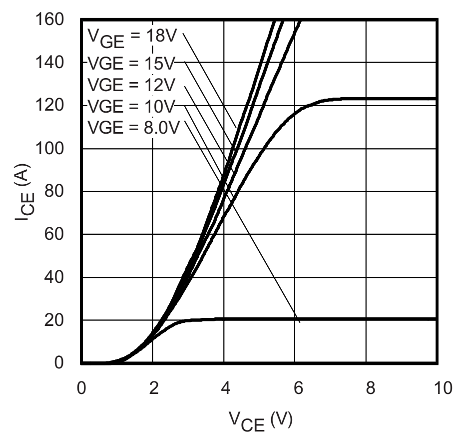


Fig. 5 - Typical IGBT Output Characteristics
T_J = - 40 °C; t_p = 80 µs

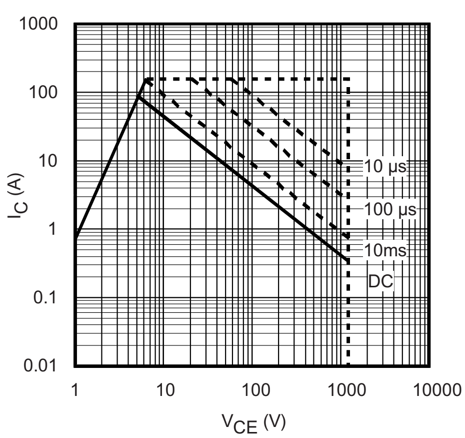


Fig. 3 - Forward SOA
T_C = 25 °C; $T_J \leq$ 150 °C

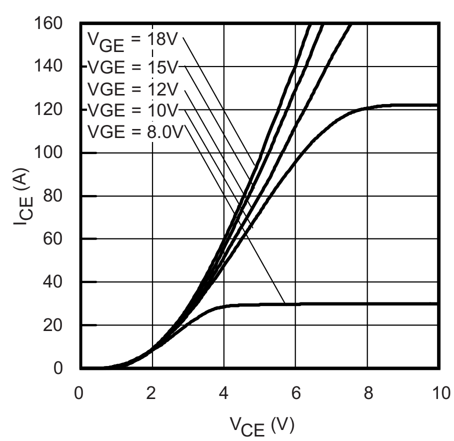


Fig. 6 - Typical IGBT Output Characteristics
T_J = 25 °C; t_p = 80 µs

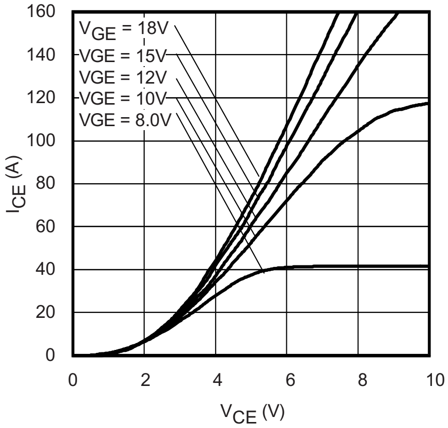


Fig. 7 - Typical IGBT Output Characteristics
T_J = 125 °C; t_p = 80 µs

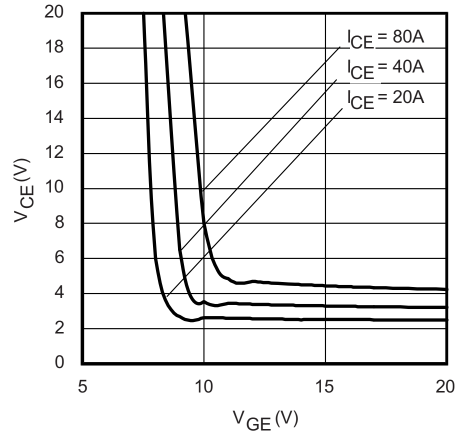


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 25 °C

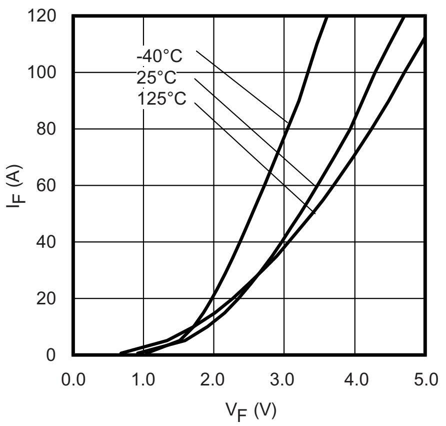


Fig. 8 - Typical Diode Forward Characteristics
t_p = 80 µs

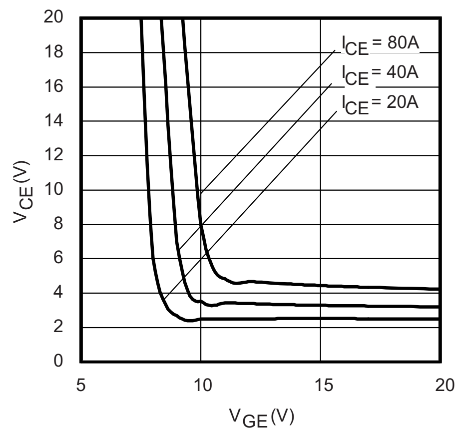


Fig. 11 - Typical V_{CE} vs. V_{GE}
T_J = 125 °C

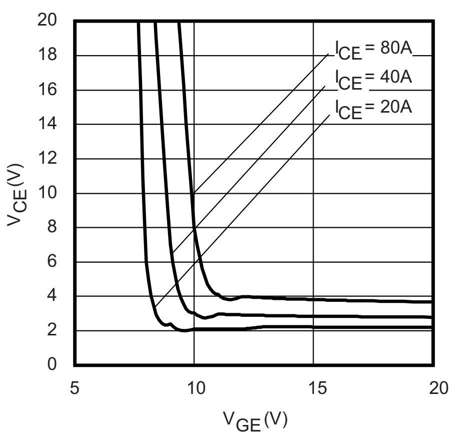


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = - 40 °C

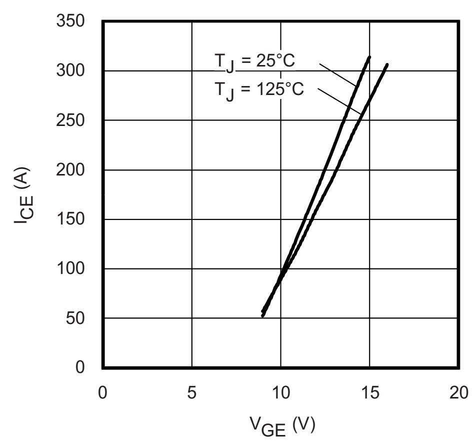


Fig. 12 - Typical Transfer Characteristics
V_{CE} = 50 V; t_p = 10 µs

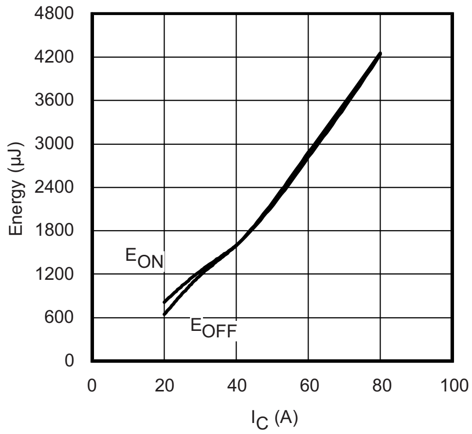


Fig. 13 - Typical Energy Loss vs. I_C
T_J = 125 °C; L = 250 μH; V_{CE} = 400 V
R_g = 5 Ω; V_{GE} = 15 V

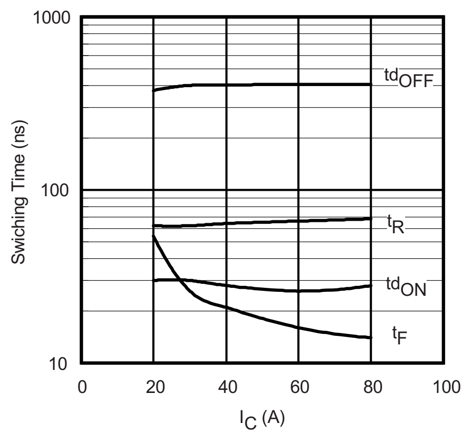


Fig. 14 - Typical Switching Time vs. I_C
T_J = 125 °C; L = 250 μH; V_{CE} = 400 V
R_g = 5 Ω; V_{GE} = 15 V

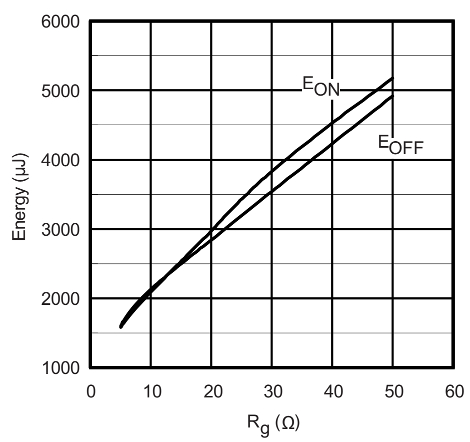


Fig. 15 - Typical Energy Loss vs. R_g
T_J = 150 °C; L = 250 μH; V_{CE} = 600 V
I_{CE} = 40 A; V_{GE} = 15 V

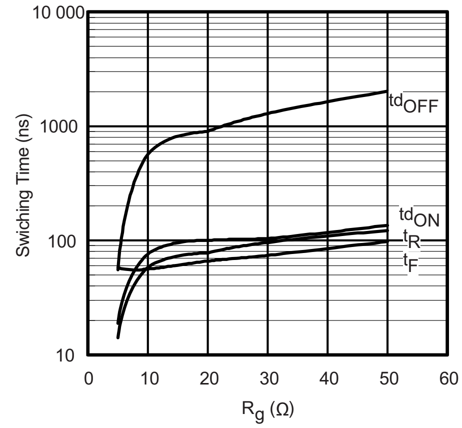


Fig. 16 - Typical Switching Time vs. R_g
T_J = 150 °C; L = 250 μH; V_{CE} = 600 V
I_{CE} = 40 A; V_{GE} = 15 V

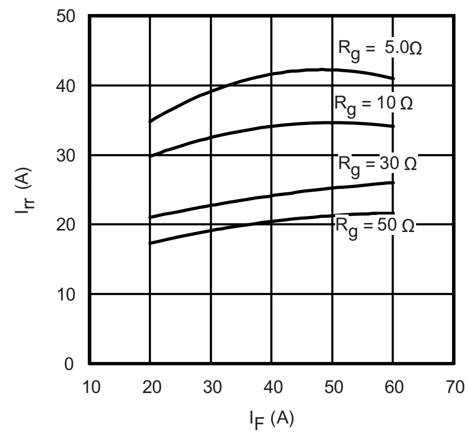


Fig. 17 - Typical Diode I_{rr} vs. I_F
T_J = 125 °C

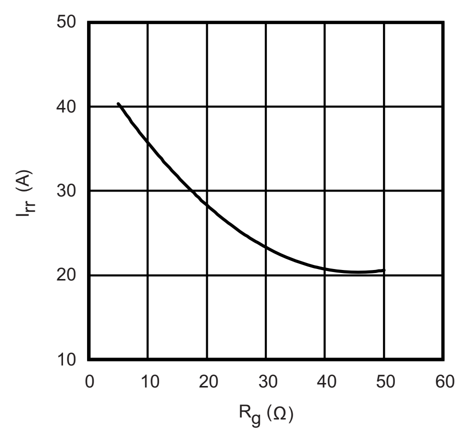


Fig. 18 - Typical Diode I_{rr} vs. R_g
T_J = 125 °C; I_F = 40 A

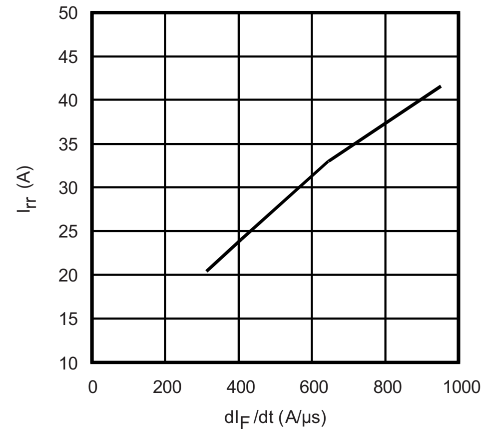


Fig. 19 - Typical Diode I_{rr} vs. dI_F/dt
V_{CC} = 600 V; V_{GE} = 15 V; I_{CE} = 40 A; T_J = 125 °C

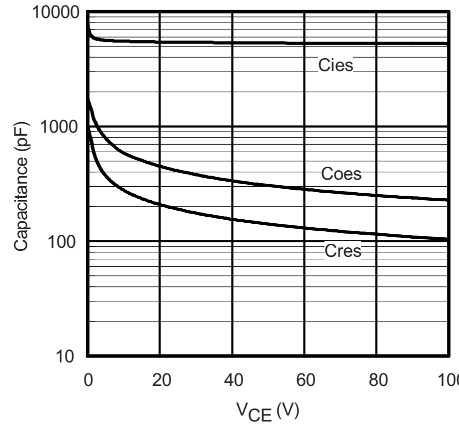


Fig. 21 - Typical Capacitance vs. V_{CE}
V_{GE} = 0 V; f = 1 MHz

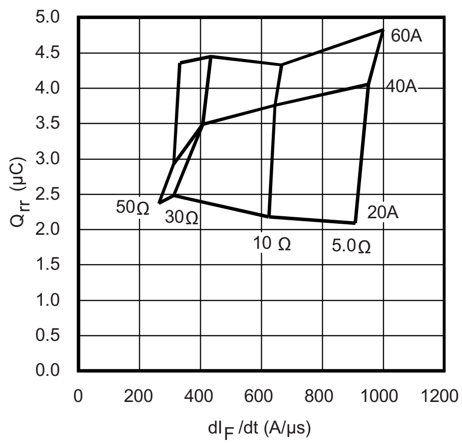


Fig. 20 - Typical Diode Q_{rr} vs. dI_F/dt
V_{CC} = 600 V; V_{GE} = 15 V; T_J = 125 °C

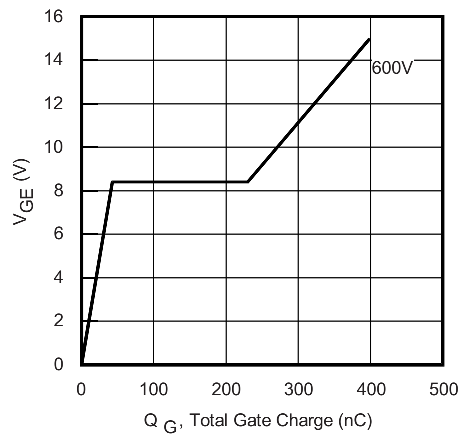


Fig. 22 - Typical Gate Charge vs. V_{GE}
I_{CE} = 5.0 A; L = 600 µH

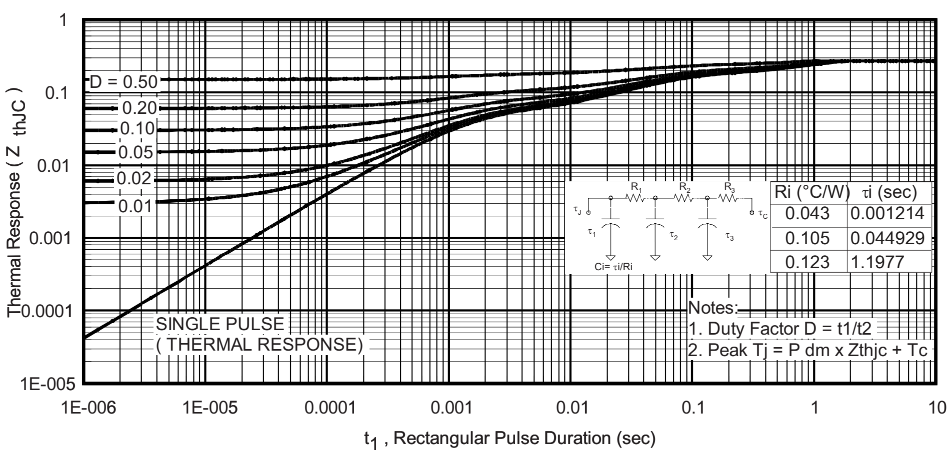


Fig. 23 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

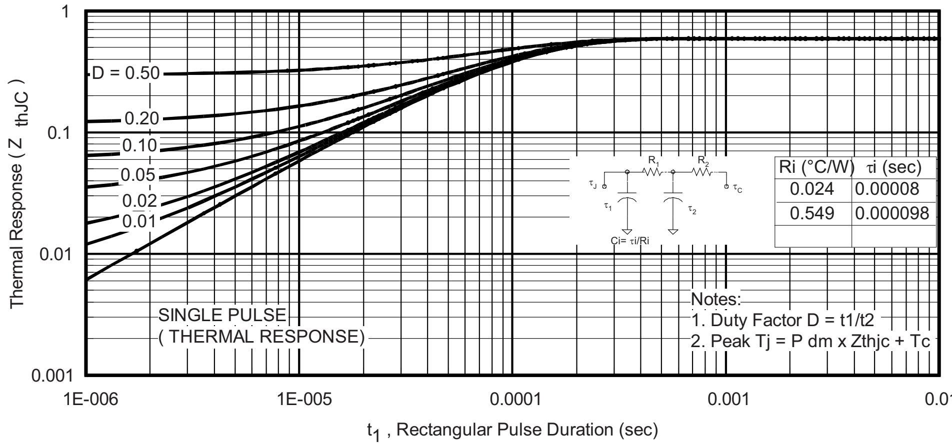


Fig. 24 - Maximum Transient Thermal Impedance, Junction to Case (Diode)

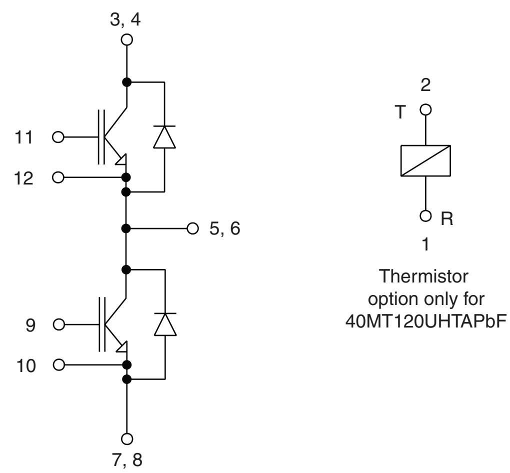


Fig. 25 - Electrical diagram

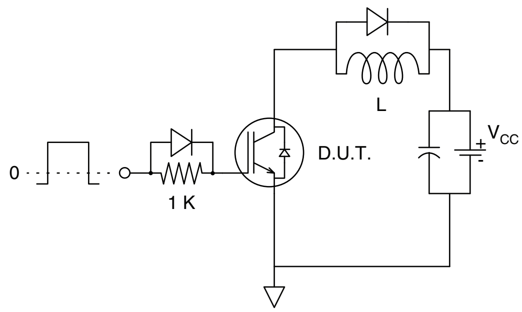


Fig. CT.1 - Gate Charge Circuit (Turn-Off)

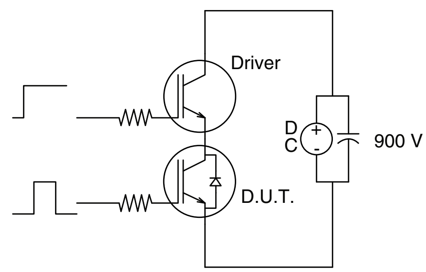


Fig. CT.3 - S.C. SOA Circuit

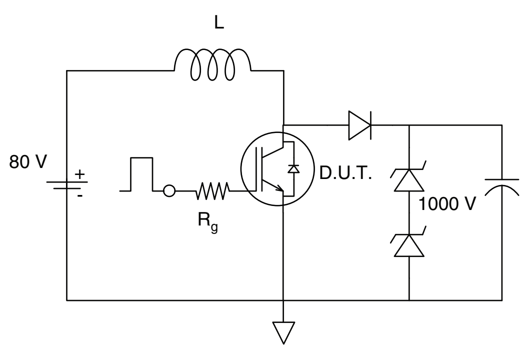


Fig. CT.2 - RBSOA Circuit

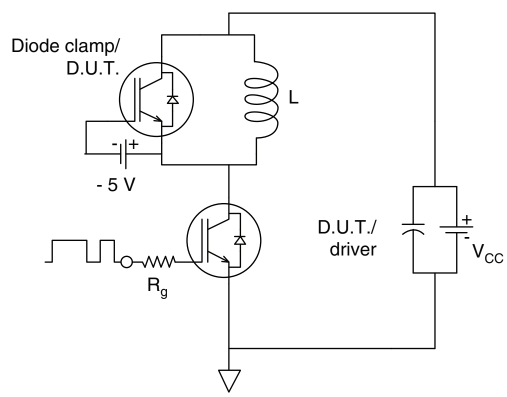


Fig. CT.4 - Switching Loss Circuit

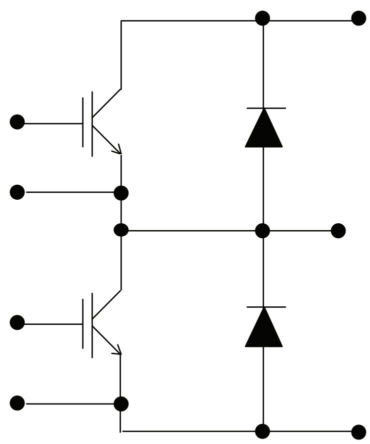
ORDERING INFORMATION TABLE

Device code	VS-	40	MT	120	U	H	T	A	PbF
	1	2	3	4	5	6	7	8	9

1 - Vishay Semiconductors product
2 - Current rating (40 = 40 A)
3 - Essential part number
4 - Voltage code (120 = 1200 V)
5 - Speed/type (U = Ultrafast IGBT)
6 - Circuit configuration (H = Half bridge)
7 - Special option:
- None = No special option
- T = Thermistor

8 - A = Al_2O_3 DBC substrate
9 - PbF = Lead (Pb)-free

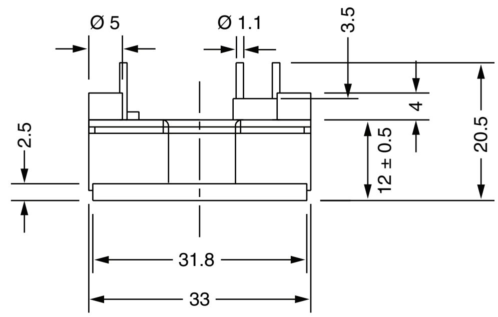
CIRCUIT CONFIGURATION

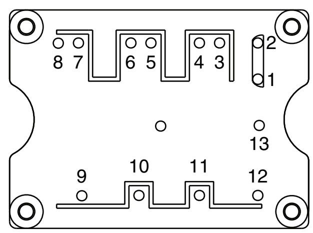


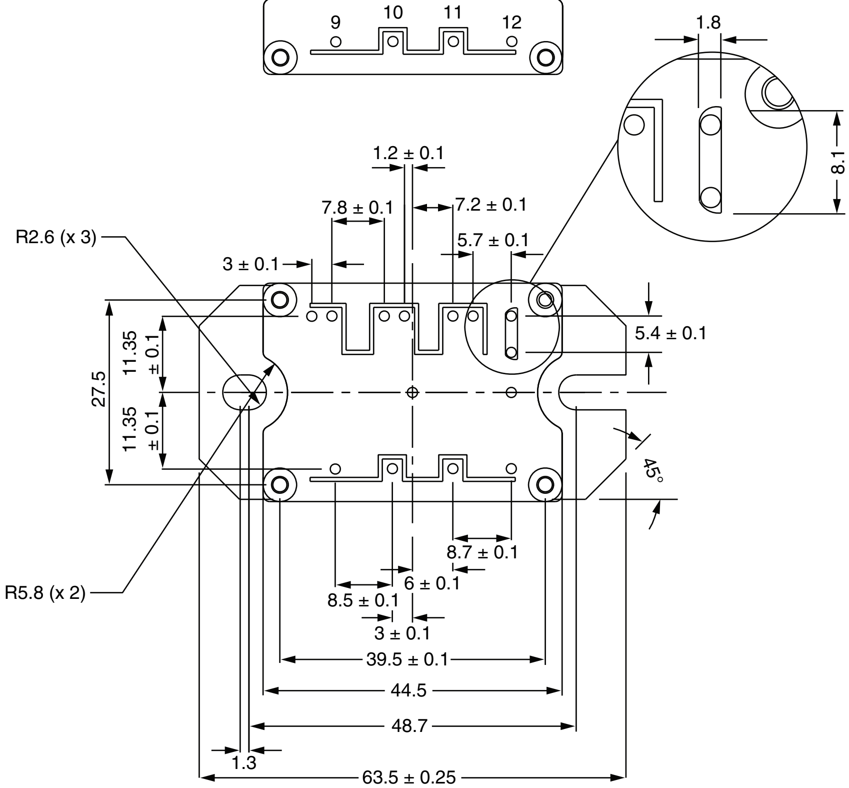
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95175

MTP

DIMENSIONS in millimeters







Note

- Unused terminals are not assembled in the package

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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